

DIALOG(R)File 352:Derwent WPI
(c) 2001 Derwent Info Ltd. All rts. reserv.

007846694

WPI Acc No: 1989-111806/198915

MOS transistor mfr - in which device control is improved by forming 1st and 2nd gate insulation films by thermal oxidn. NoAbstract Dwg 7/9

Patent Assignee: SONY CORP (SONY)

Number of Countries: 001 Number of Patents: 001

Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Week
JP 1059866	A	19890307	JP 87216588	A	19870831	198915 B

Priority Applications (No Type Date): JP 87216588 A 19870831

Patent Details:

Patent No	Kind	Lan Pg	Main IPC	Filing Notes
JP 1059866	A	8		

Title Terms: MOS; TRANSISTOR; MANUFACTURE; DEVICE; CONTROL;
IMPROVE; FORMING; GATE; INSULATE; FILM; THERMAL; OXIDATION;
NOABSTRACT

Index Terms/Additional Words: METAL; OXIDE; SEMICONDUCTOR

Derwent Class: L03; U11; U12; U13

International Patent Class (Additional): H01L-027/12; H01L-029/78

File Segment: CPI; EPI